1. Scope :

This specification applies to N/P/N silicon zener double diodes chips,
Device NO. SD-00811GNL

2. Structure :

2-1. Planar type : N/P/N.
2-2. Electrodes :
Top side : Gold pad.
Back side : Gold layer.

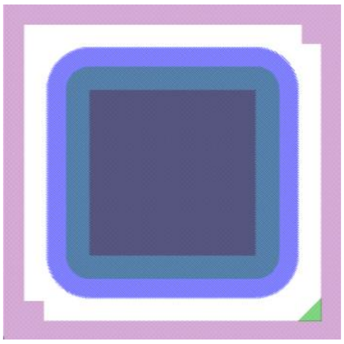
3. Size :

3-1. ※1Chip size : 8.5 mils x 8.5 mils (0.215 mm x 0.215 mm).
3-2. Chip thickness : 6.0 ± 1.0 mils (0.150 ± 0.025 mm).
3-3. Bonding pad : 5.9 mils x 5.9 mils (0.150 mm x 0.150 mm) .
3-4. Pattern drawing : Refer to the attached drawing.

※1Including scribing line. The chip size is about $(0.190\pm0.015)^2mm^2$ after dicing.
※2 The bonding pad dimension is $(0.150\pm0.005)^2mm^2$.

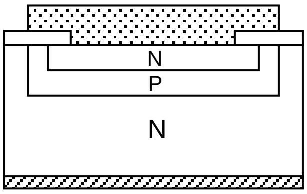
4. Electrical characteristics (Ta = 25 ℃)

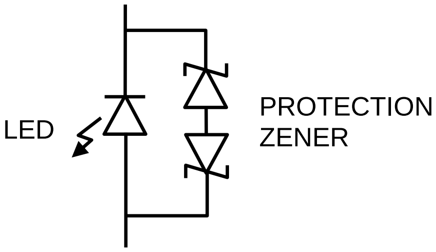
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Leakage Current	Idf	V=5V Ee=0mW/cm^2			500	nA
	Idr	V=5V Ee=0mW/cm^2			500	
Zener Voltage	Vz(forward)	Izf=5mA Ee=0mW/cm^2	5.2		8.0	V
	Vz(reverse)	Izr=5mA Ee=0mW/cm^2	8.0		13.0	



5. Annotation :

5-1. Parallel with one LED
5-2. Single pad (one wire bonding applied only)
5-3. Double direction Zener diode protection





Equivalent Circuit